



**General Description:**

- (1) Chip Dimension  
 Chip Size= 13 mil x 10 mil (325um x 250um)  
 Chip Thickness = 100±10μm  
 P/N Bonding Pad = 85±5μm
- (2) Electrode:  
 P (Anode) → Au  
 N (Cathode) → Au
- (3) Structure:  
 Refer to drawing

**Electro-optical Characteristics(Ta=RT)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage	V <sub>F</sub>	2.8	-	3.5	V	I <sub>F</sub> =20mA
Dominant Wavelength	λ <sub>D</sub>	450	460	475	nm	I <sub>F</sub> =20mA
Reverse Current	I <sub>R</sub>	0	-	2	μA	V <sub>R</sub> =-5V

Luminous Intensity( I <sub>v</sub> ) mcd at I <sub>F</sub> =20mA	Dominant Wavelength(nm)											
	44C: 445~447.5	44D: 447.5~450	45A: 450~452.5	45B: 452.5~455	45C: 455~457.5	45D: 457.5~460	46A: 460~462.5	46B: 462.5~465	46C: 465~467.5	46D: 467.5~470	47A: 470~472.5	47B: 472.5~475
Range												
B: 30~40												
C: 40~50			*	*	*	*						
D: 50~60			*	*	*	*						
E: 60~70			*	*	*	*	*	*	*	*	*	*
F: 70~80			*	*	*	*	*	*	*	*	*	*
G: 80~90					*	*	*	*	*	*	*	*
H: 90~100					*	*	*	*	*	*	*	*
I: 100~120							*	*	*	*	*	*
J: 120~140										*	*	*
K: 140~160											*	*
L: 160~180												
M: 180~200												
N: 200~240												

**Notes:**

**Features:**

- 1. High Luminous Intensity
- 2. Long Operation Life
- 3. High Current; Pulse Operation
- 4. Indoor/Outdoor Applications

- 1. Dominant wavelength includes an error of ± 1nm
- 2. Luminous intensity includes an error of ±10%
- 3. Luminous intensity is measured on bare chip
- 4. InGaN LED is sensitive to ESD
- \* MODEL NO: SN XXX 12J X

